FAIRCHILD SEMICONDUCTOR®

October 2013

FDPF2710T

N-Channel PowerTrench® MOSFET
250 V, 25 A, 42.5 mΩ

Features

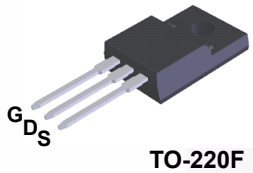
- $R_{DS(on)}$ = 36.3 mΩ (Typ.)@ V_{GS} = 10 V, I_D = 25 A
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

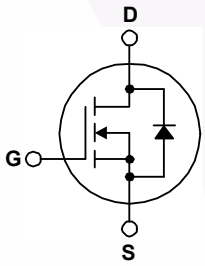
This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Consumer Appliances
- Synchronous Rectification



TO-220F



Absolute Maximum Ratings

Symbol	Parameter		FDPF2710T	Unit
V_{DS}	Drain-Source Voltage		250	V
V_{GS}	Gate-Source voltage		± 30	V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	25 18.8	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	100	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	62.5 0.5	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDPF2710T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDPF2710T	FDPF2710T	TO-220F	Tube	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25°C	250	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.25	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250V, V_{GS} = 0V V_{DS} = 250V, V_{GS} = 0V,T_C = 125°C	-- --	-- --	10 500	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	3.9	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 25A	--	36.3	42.5	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 25A	--	63	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	--	5470	7280	pF
C_{oss}	Output Capacitance		--	426	567	pF
C_{rss}	Reverse Transfer Capacitance		--	97	146	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125V, I_D = 50A V_{GS} = 10V, R_{GEN} = 25Ω	--	80	170	ns
t_r	Turn-On Rise Time		--	252	514	ns
$t_{d(off)}$	Turn-Off Delay Time		--	112	234	ns
t_f	Turn-Off Fall Time	(Note 4)	--	154	318	ns
Q_g	Total Gate Charge	V_{DS} = 125V, I_D = 50A V_{GS} = 10V	--	78	101	nC
Q_{gs}	Gate-Source Charge		--	34	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4)	--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	25	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	150	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 25A	--	--	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 50A dI_F/dt =130A/μs	--	163	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.3	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1mH, I_{AS} = 17A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 50A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

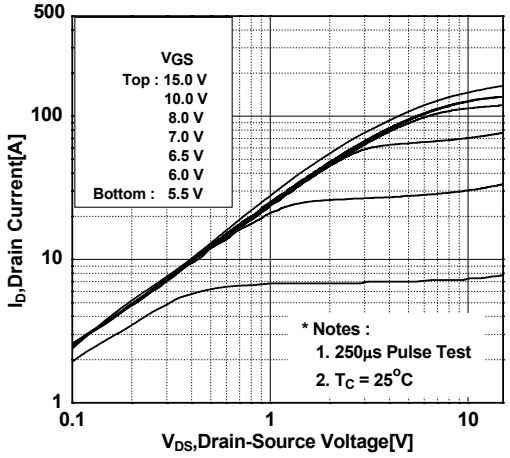


Figure 2. Transfer Characteristics

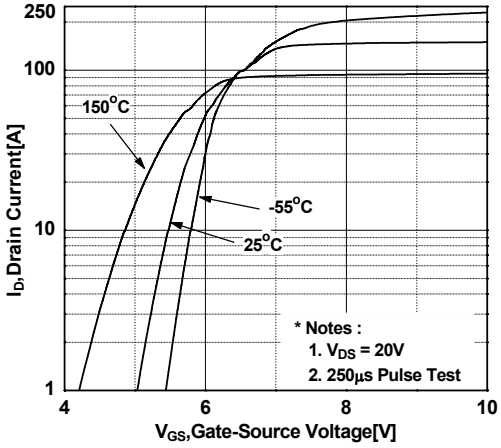


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

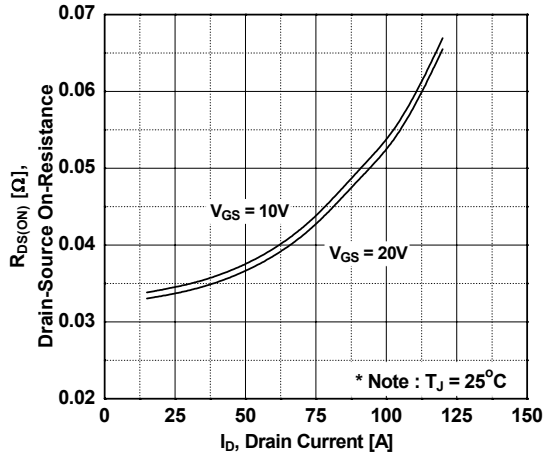


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

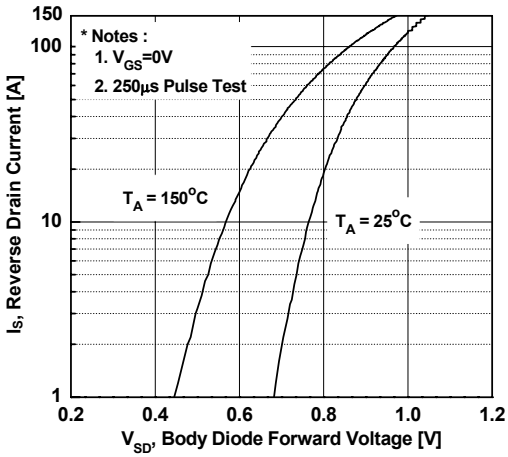


Figure 5. Capacitance Characteristics

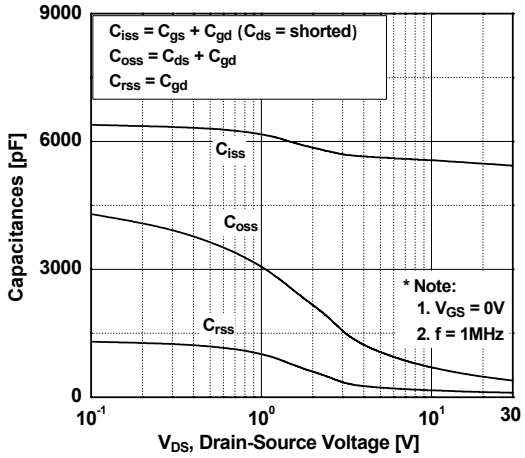
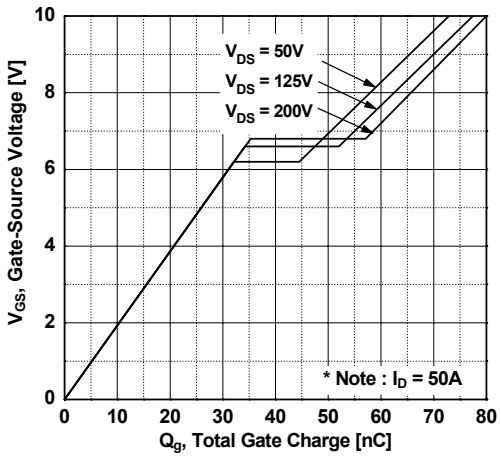


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

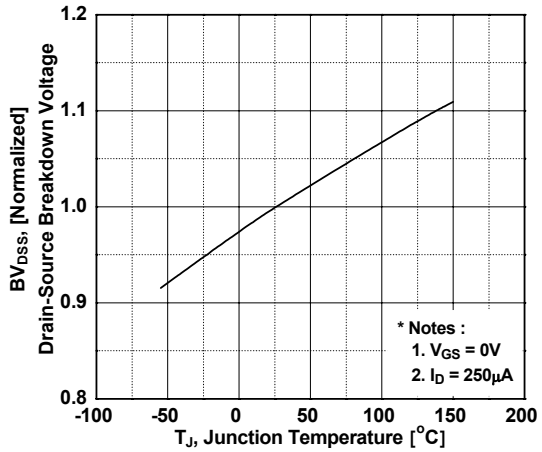


Figure 8. On-Resistance Variation vs. Temperature

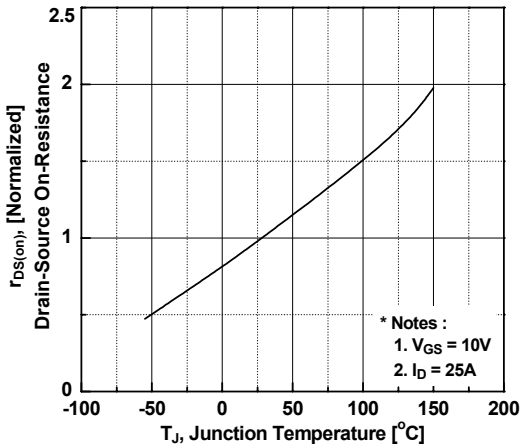


Figure 9. Maximum Safe Operating Area

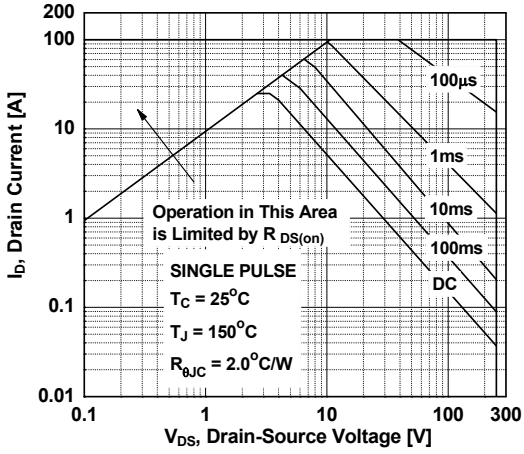


Figure 10. Maximum Drain Current vs. Case Temperature

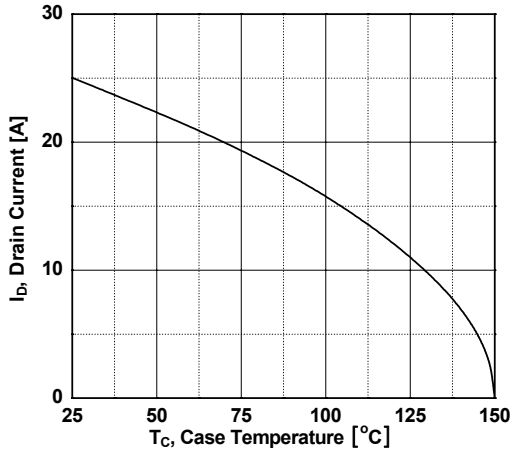


Figure 11. Transient Thermal Response Curve

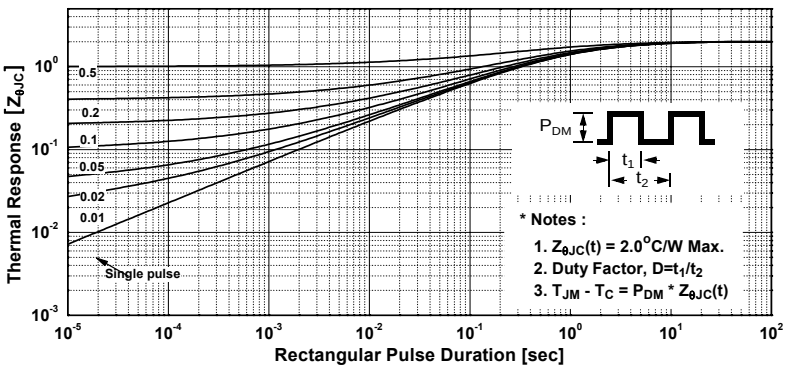


Figure 12. Gate Charge Test Circuit & Waveform

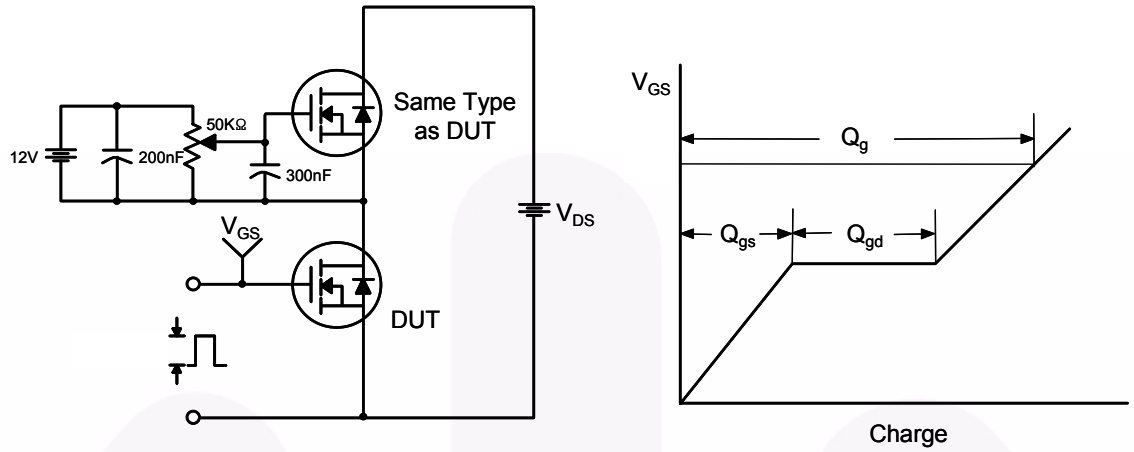


Figure 13. Resistive Switching Test Circuit & Waveforms

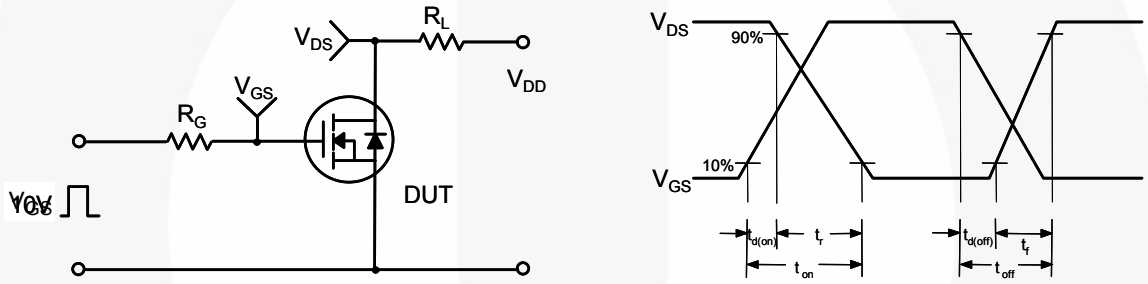


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

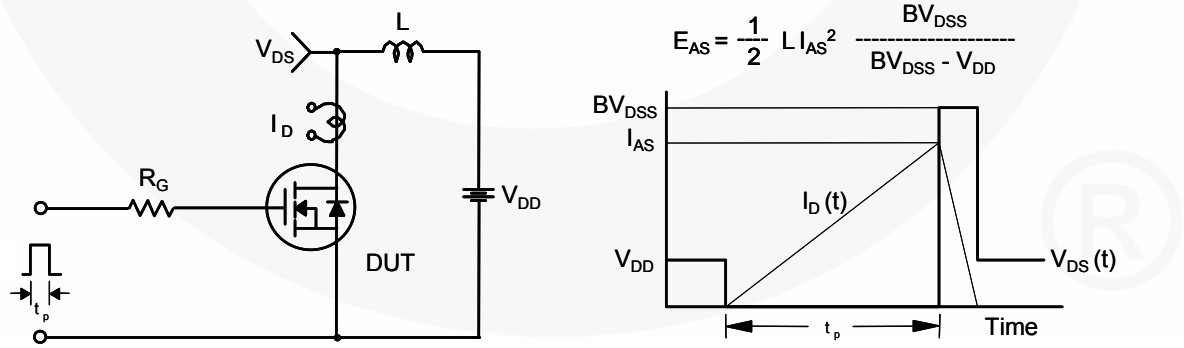
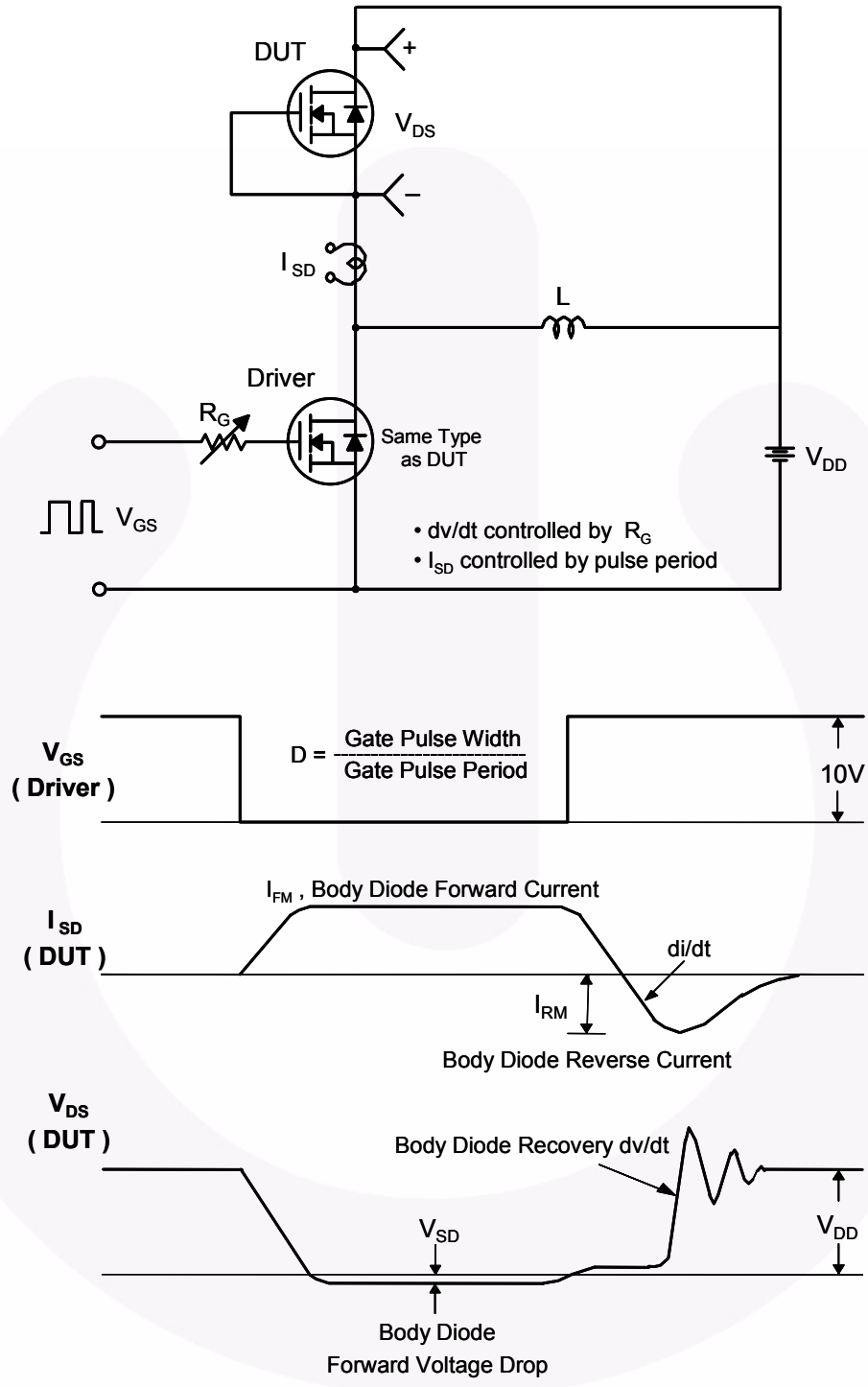


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

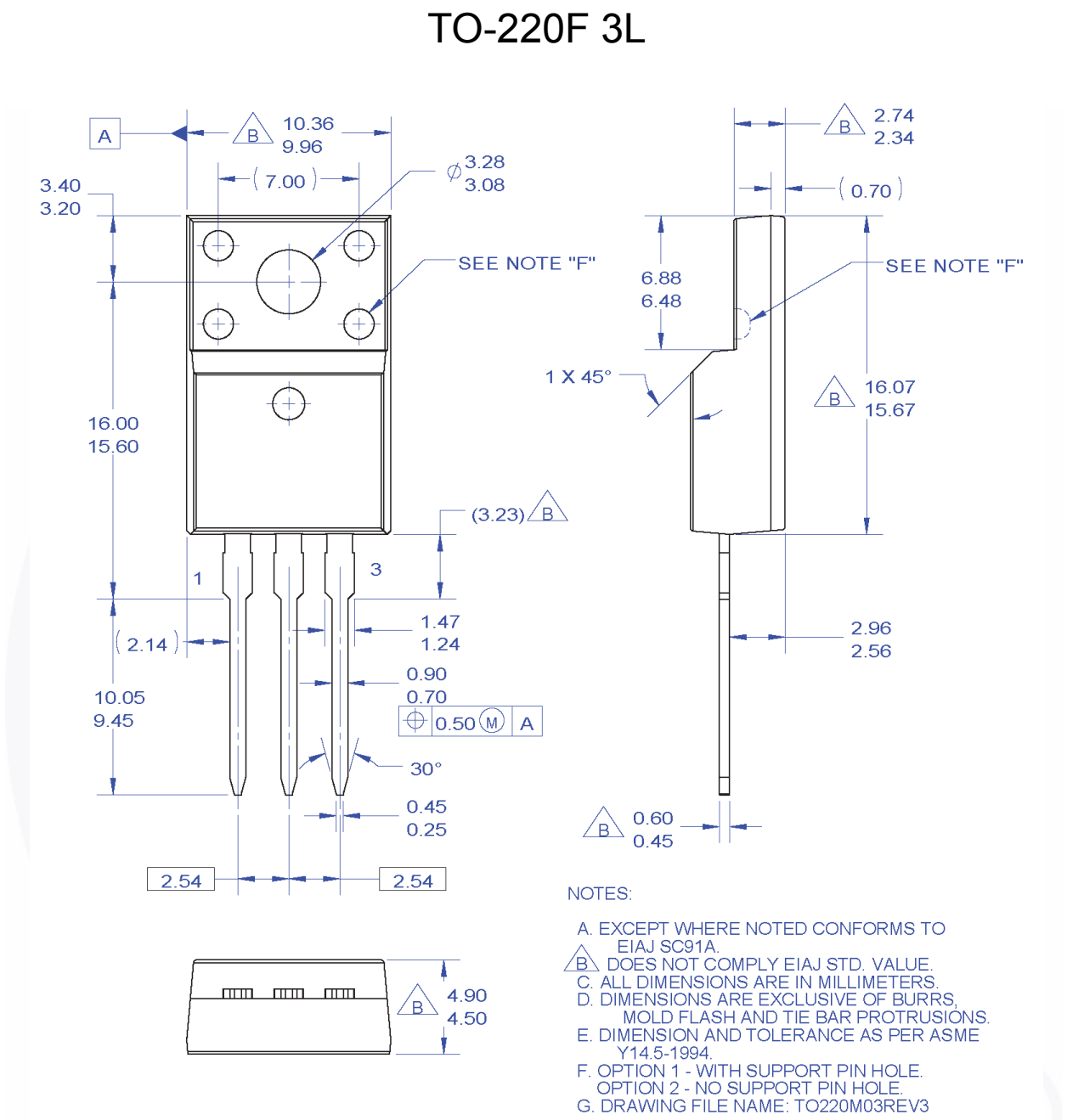


Figure 16. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Straight Lead

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Dimension in Millimeters

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Rev. I66